

SHENZHEN YIXINWEI TECHNOLOGY CO.,LTD

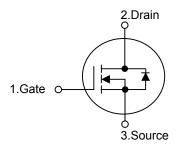
UT30N03 Power MOSFET

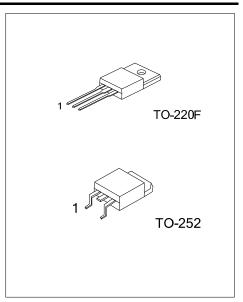
N-CHANNEL ENHANCEMENT MODE

■ FEATURES

- * $R_{DS(ON)} = 30 m\Omega @V_{GS} = 10 V$
- * Low Capacitance
- * Optimized gate charge
- * Fast switching capability
- * Avalanche energy specified

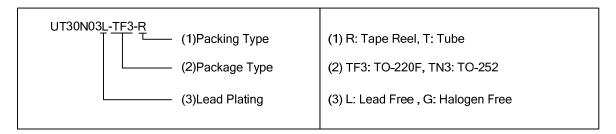
■ SYMBOL





■ ORDERING INFORMATION

	Ordering Number		Dookogo	Pin Assignment			Dooking	
	Lead Free	Halogen Free	Package	1	2	3	Packing	
U	JT30N03L-TF3-T	UT30N03G-TF3-T	TO-220F	G	D	S	Tube	
U	IT30N03L-TN3-R	UT30N03G-TN3-R	TO-252	G	D	S	Tape Reel	
U	JT30N03L-TN3-T	UT30N03G-TN3-T	TO-252	G	D	S	Tube	



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■ **ABSOLUTE MAXIMUM RATINGS** (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current		I_{D}	30	Α
Pulsed Drain Current		I _{DM}	40	Α
Avalanche Energy	E _{AS}	90	mJ	
Down Discipation	TO-220F	Б	47	W
Power Dissipation	TO-252	P _D	42	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
lunction to Ambient	TO-220F	0	62.5	°C/W
Junction-to-Ambient	TO-252	θ_{JA}	110	°C/W
lunction to Coop	TO-220F	0	2.66	°C/W
Junction-to-Case	TO-252	$\theta_{ m JC}$	3.0	°C/W

■ **ELECTRICAL CHARACTERISTICS** (T_J =25°C, unless otherwise specified)

1		1							
PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V			
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ			
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA			
ON CHARACTERISTICS									
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0			V			
Static Drain-Source On-State Resistance	נ	V _{GS} = 10 V, I _D = 15 A		20	30	mΩ			
(Note2)	$R_{DS(ON)}$	V_{GS} = 4.5 V, I_D = 12.5 A		30	45	mΩ			
DYNAMIC CHARACTERISTICS									
Input Capacitance	C _{ISS}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1MHz		1170		рF			
Output Capacitance	Coss			320		рF			
Reverse Transfer Capacitance	C _{RSS}			60		рF			
SWITCHING CHARACTERISTICS									
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 15V$, $I_D = 30A$, $R_L = 0.5\Omega$,		10	20	ns			
Turn-On Rise Time	t _R			10	20	ns			
Turn-Off Delay Time	t _{D(OFF)}	V_{GS} =10V, R_G =7.5 Ω		25	40	ns			
Turn-Off Fall Time	t _F	(Note 4, 5)		15	30	ns			
Total Gate Charge	Q_G			18	35	nC			
Gate-Source Charge	Q_{GS}	V_{DS} = 15V, I_{D} = 30A, V_{GS} = 10 V		5.5		nC			
Gate-Drain Charge	Q_GD	(Note 4, 5)		2		nC			
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS									
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} = 0 V, I _F = 30A		1.1	1.5	V			
Maximum Continuous Drain-Source Diode					20	_			
Forward Current	I _S				30	Α			
Maximum Pulsed Drain-Source Diode	1				40	Α			
Forward Current	I _{SM}				40	А			
Reverse Recovery Time	t_{RR}	I _F =30A, dI _F /dt=100A/μs		50	100	ns			

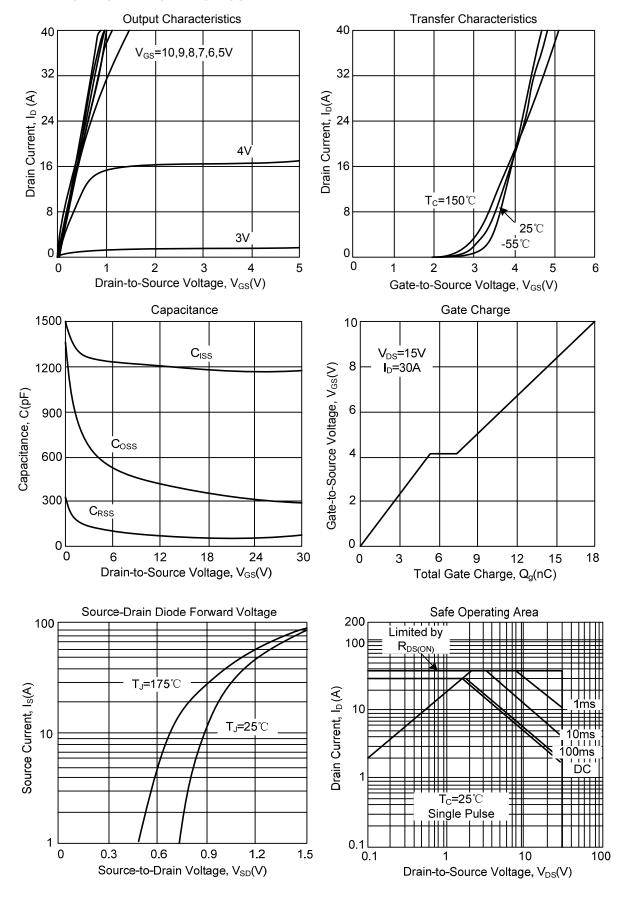
Notes: 1. Guaranteed by design, not subject to production testing.

- 2. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%
- 3. Essentially independent of operating temperature

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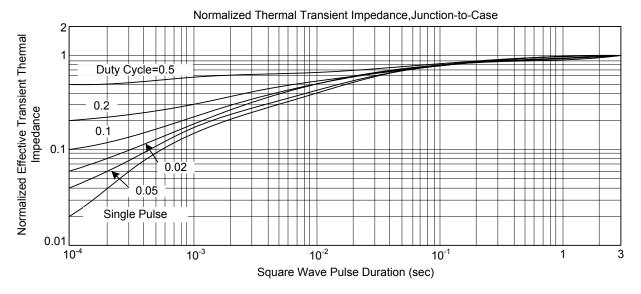
TYPICAL CHARACTERISTICS

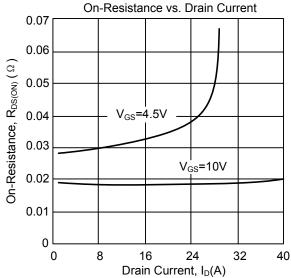


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■ TYPICAL CHARACTERISTICS(Cont)





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